U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Serial No.
	M-15171 US	10/631,941
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant	
(Use several sheets if necessary)	Yi Ding	
	Filing Date	Group
	July 30, 2003	2812

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*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
WLL	AA	6,265,739	Jul. 2001	Yaegashi et al.			
WLL	AB	6,747,310	Jun. 2004	Fan et al.			
WLL	AC	2003/0205776	Nov. 2003	Yaegashi et al.			
WLL	AD	6,468,865	Oct. 2002	Yang et al.			
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WLL	AO	5,705,415	Jan. 1998	Orlowski et al.			
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Examiner WLL Date Considered 5/26/05

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	AG						
	AH						

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							Translation	
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WLL	AI	EP 0 938 098 A2	25 Aug. 1999	Europe				
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	AK							
	AL							

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WLL	AM	United States Patent Application No. 10/798,475, entitled "Fabrication of Conductive Lines Interconnecting Conductive Gates in Nonvolatile Memories and Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15296 US.
WLL	AN	United States Patent Application No. 10/797,972, entitled "Fabrication of Conductive Lines Interconnecting First Conductive Gates in Nonvolatile Memories Having Second Conductive Gates Provided By Conductive Gates Lines, Wherein The Adjacent Conductive Gate Lines For The Adjacent Columns Are Spaced From Each Other, And Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No. M-15297 US.
	AO	
	AP	

Examiner Walter Lee | Date Considered 5/26/05

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WLL	AR	United States Patent Application No. 10/440,466, entitled "Fabrication Of Conductive Gates For Nonvolatile Memories From Layers With Protruding Portions," Filed on May 16, 2003; Attorney Docket No.: M-12979 US.
WLL	AS	United States Patent Application No. 10/440,005, entitled "Fabrication of Dielectric On A Gate Surface To Insulate The Gate From Another Element Of An Integrated Circuit," Filed on May 16, 2003; Attorney Docket No.: M-15203 US.
WLL	AT	United States Patent Application No. 10/440,508, entitled "Fabrication Of Gate Dielectric In Nonvolatile Memories Having Select, Floating And Control Gates," Filed on May 16, 2003; Attorney Docket No.: M-15204 US.
WLL	AU	United States Patent Application No. 10/440,500, entitled "Integrated Circuits With Openings that Allow Electrical Contact To Conductive Features Having Self-Aligned Edges," Filed on May 16, 2003; Attorney Docket No.: M-15205 US.

Examiner Nath L. Tinsley Date Considered 5/20/05

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WLL	AW	United States Patent Application No. 10/411,813, entitled "Nonvolatile Memories With A Floating Gate Having An Upward Protrusion," Filed on April 10, 2003; Attorney Docket No.: M-12903 US.
WLL	AX	United States Patent Application No. 10/393,202, entitled "Fabrication of Integrated Circuit Elements In Structures With Protruding Features," Filed on March 19, 2003; Attorney Docket No.: M-15151 US.
WLL	AY	United States Patent Application No. 10/632,155, entitled "Nonvolatile Memory Cells With Buried Channel Transistors," Filed on July 30, 2003; Attorney Docket No.: M-15222 US.
WLL	AZ	United States Patent Application No. 10/632,007, entitled "Arrays Of Nonvolatile Memory Cells Wherin Each Cell Has Two Conductive Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15223 US.
WLL	BA	United States Patent Application No. 10/631,452, entitled "Fabrication Of Dielectric For A Nonvolatile Memory Cell Having Multiple Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15229 US.
WLL	BB	United States Patent Application No. 10/632,154, entitled "Fabrication Of Gate Dielectric In Nonvolatile Memories In Which A Memory Cell Has Mutiple Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15230 US.
WLL	BC	United States Patent Application No. 10/631,552, entitled "Nonvolatile Memories And Methods Of Fabrication," Filed on July 30, 2003; Attorney Docket No.: M-12902-1P US.
WLL	BD	United States Patent Application No. 10/632,186, entitled "Nonvolatile Memory Cell With Multiple Floating Gates Formed After The Select Gate And Having Upward Protrusions," Filed on July 30, 2003; Attorney Docket No.: M-15241 US.
	BE	
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	BG	
	BH	

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	Filed Herewith	Unassigned

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WLL	AN	Wu, A.T.; Chan T.Y.; Ko, P.K.; and Hu, C. "A Novel High-Speed, 5-Volt Programming EPROM Structure With Source-Side Injection," 1986 IEEE, 584-587.
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WLC	BG	Van Duuren, Michiel et al., "Compact poly-CMP Embedded Flash Memory Cells For One or Two Bit Storage," Philips Research Leuven, Kapeldreef 75, B3001 Leuven, Belgium, pages 73-74.
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